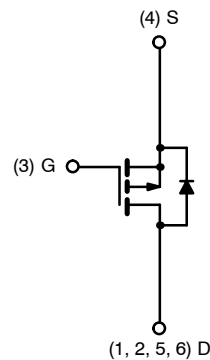
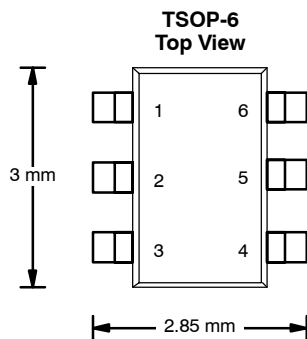


P-Channel 2.5-V (G-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
-20	0.065 @ $V_{GS} = -4.5$ V	-4.5
	0.090 @ $V_{GS} = -2.7$ V	-3.8
	0.100 @ $V_{GS} = -2.5$ V	-3.7

FEATURES

- TrenchFET® Power MOSFET
- 100% R_g Tested



Ordering Information: Si3443DV-T1—E3 (Lead Free)

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)					
Parameter	Symbol	5 secs	Steady State	Unit	
Drain-Source Voltage	V_{DS}	-20		V	
Gate-Source Voltage	V_{GS}	± 12			
Continuous Drain Current ($T_J = 150^\circ\text{C}$) ^a	I_D	$T_A = 25^\circ\text{C}$	-4.5	-3.4	A
		$T_A = 70^\circ\text{C}$	-3.6	-2.7	
Pulsed Drain Current	I_{DM}	-20			
continuous Source Current (Diode Conduction) ^a	I_S	-1.7	-0.9		
Maximum Power Dissipation ^a	P_D	$T_A = 25^\circ\text{C}$	2.0	1.1	W
		$T_A = 70^\circ\text{C}$	1.3	0.7	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150		$^\circ\text{C}$	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 5$ sec	R_{thJA}	50	62.5	$^\circ\text{C/W}$
	Steady State		90	110	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	22	30	

Notes

a. Surface Mounted on FR4 Board, $t \leq 5$ sec.

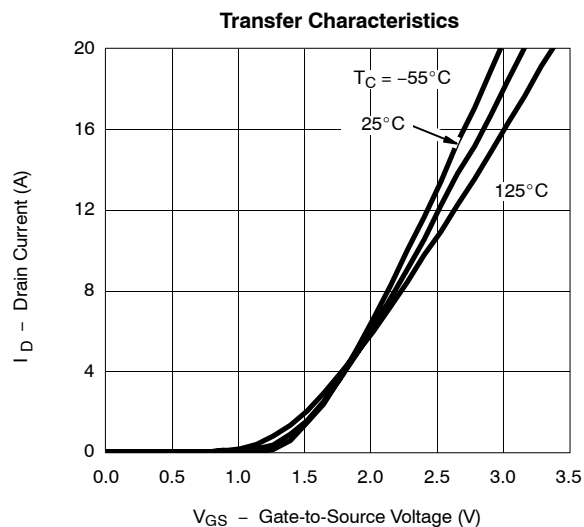
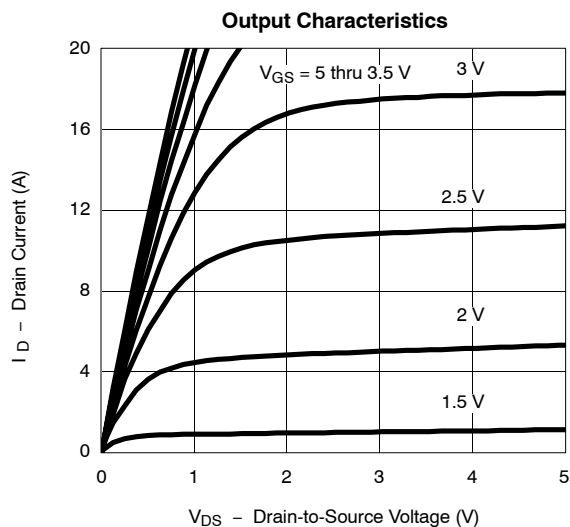
For SPICE model information via the Worldwide Web: <http://www.vishay.com/www/product/spice.htm>

SPECIFICATIONS ($T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250 \mu\text{A}$	-0.6		-1.4	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μA
		$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 70^\circ\text{C}$			-5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	-15			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = -4.5 \text{ V}, I_D = -4.5 \text{ A}$		0.050	0.065	Ω
		$V_{GS} = -2.7 \text{ V}, I_D = -3.8 \text{ A}$		0.070	0.090	
		$V_{GS} = -2.5 \text{ V}, I_D = -3.7 \text{ A}$		0.080	0.100	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -10 \text{ V}, I_D = -4.5 \text{ A}$		10		S
Diode Forward Voltage ^a	V_{SD}	$I_S = -1.7 \text{ A}, V_{GS} = 0 \text{ V}$		-0.8	-1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_D = -4.5 \text{ A}$		7.3	15	nC
Gate-Source Charge	Q_{gs}			2.0		
Gate-Drain Charge	Q_{gd}			1.9		
Gate Resistance	R_g		3		15	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10 \text{ V}, R_L = 10 \Omega$ $I_D \cong -1.0 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_g = 6 \Omega$		15	50	ns
Rise Time	t_r			32	60	
Turn-Off Delay Time	$t_{d(off)}$			50	100	
Fall Time	t_f			45	80	
Source-Drain Reverse Recovery Time	t_{rr}		$I_F = -1.7 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}$		35	

Notes

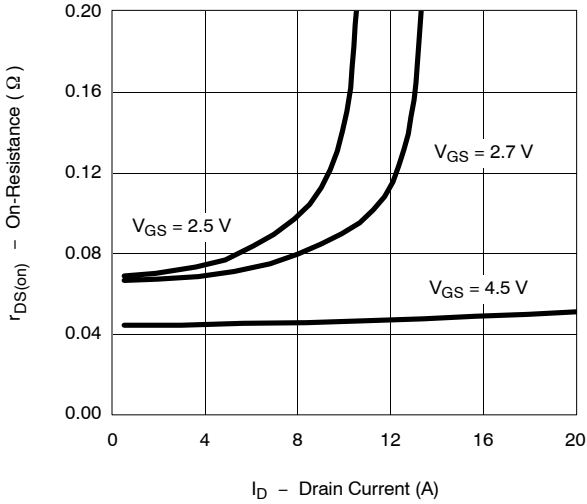
- a. Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

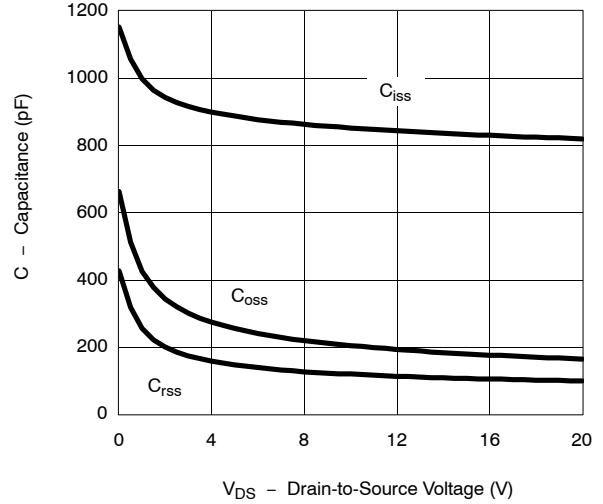


TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)

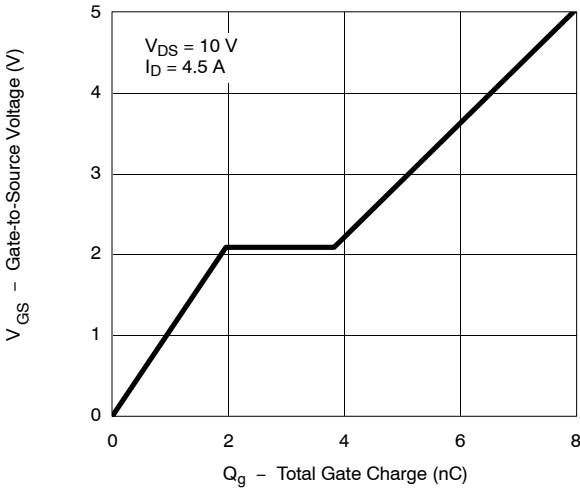
On-Resistance vs. Drain Current



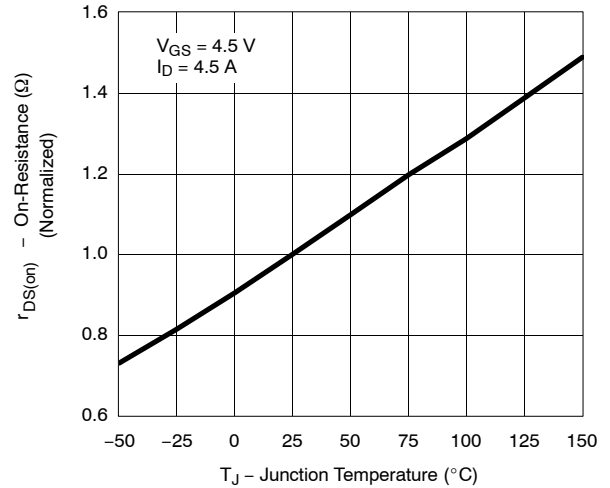
Capacitance



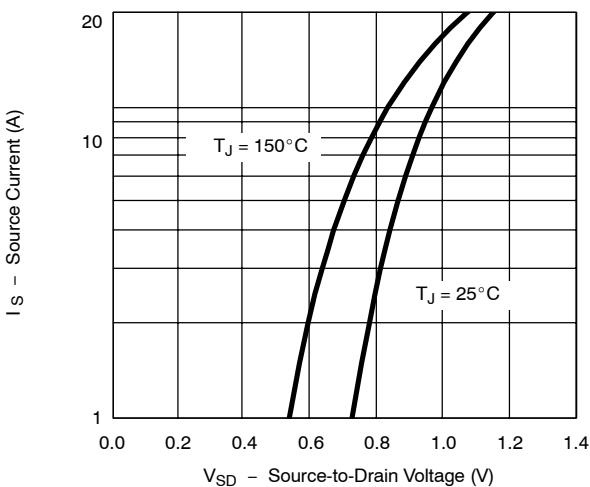
Gate Charge



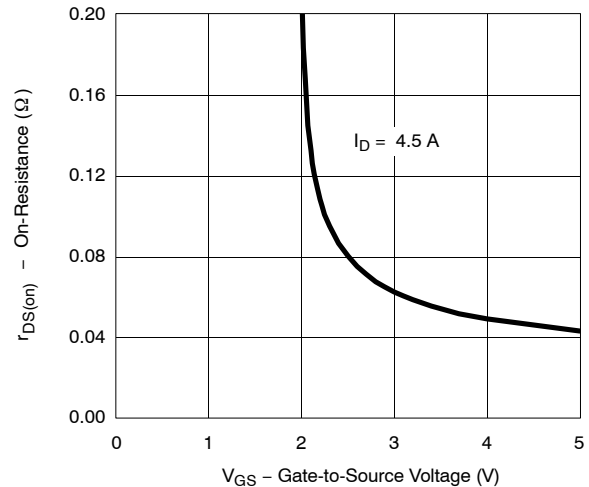
On-Resistance vs. Junction Temperature



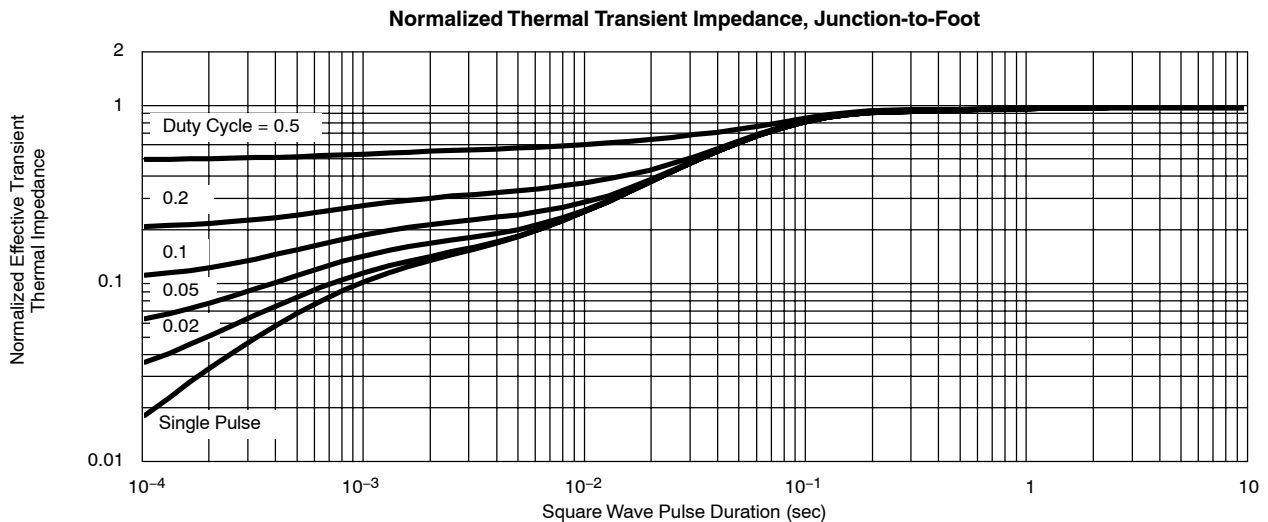
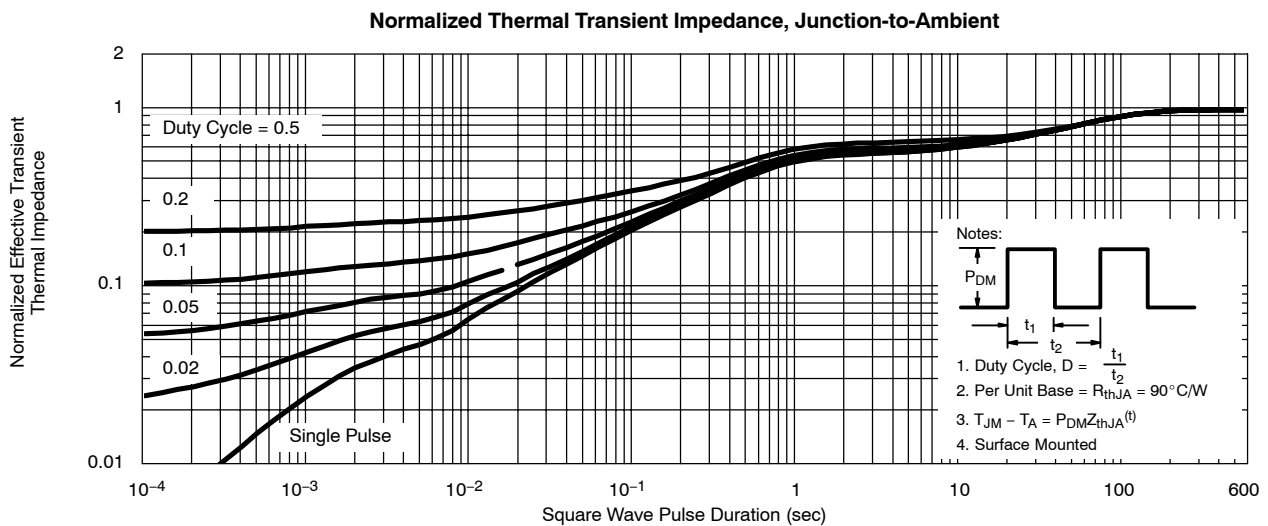
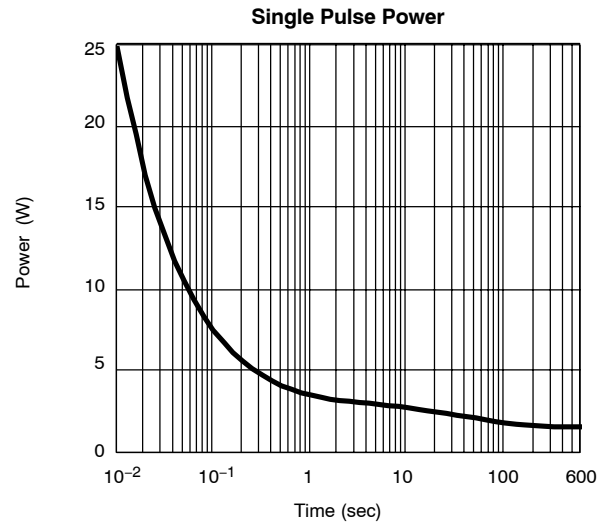
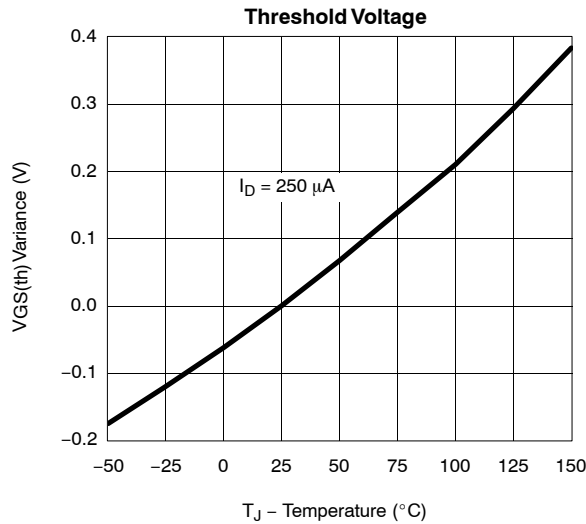
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)





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